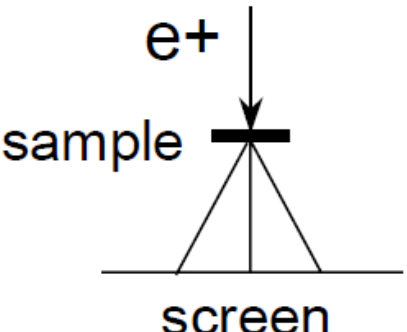
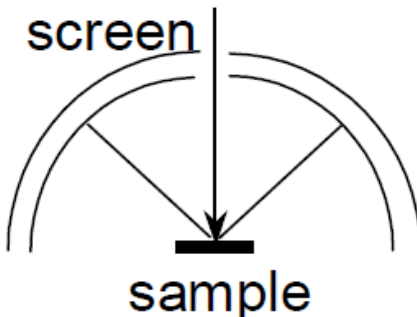
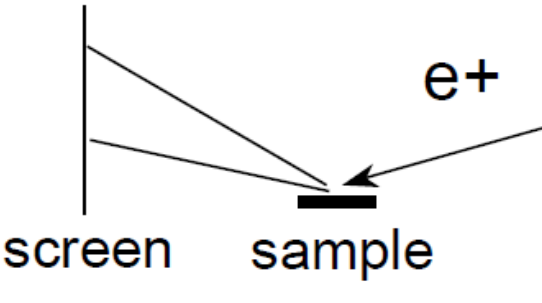


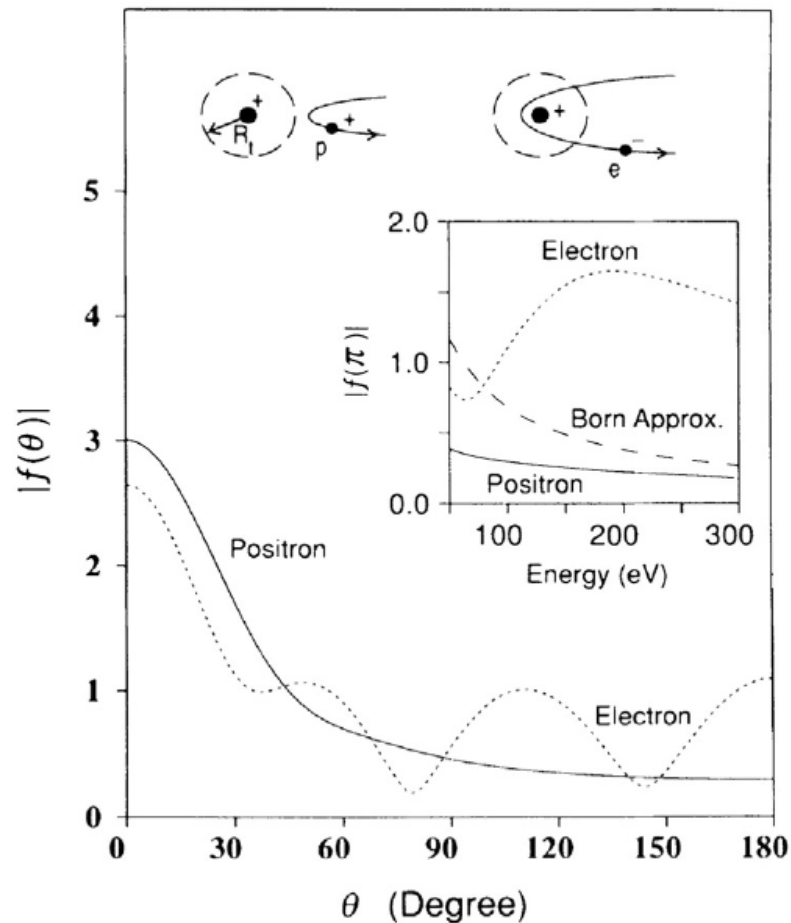
Positron diffraction

- positron diffraction

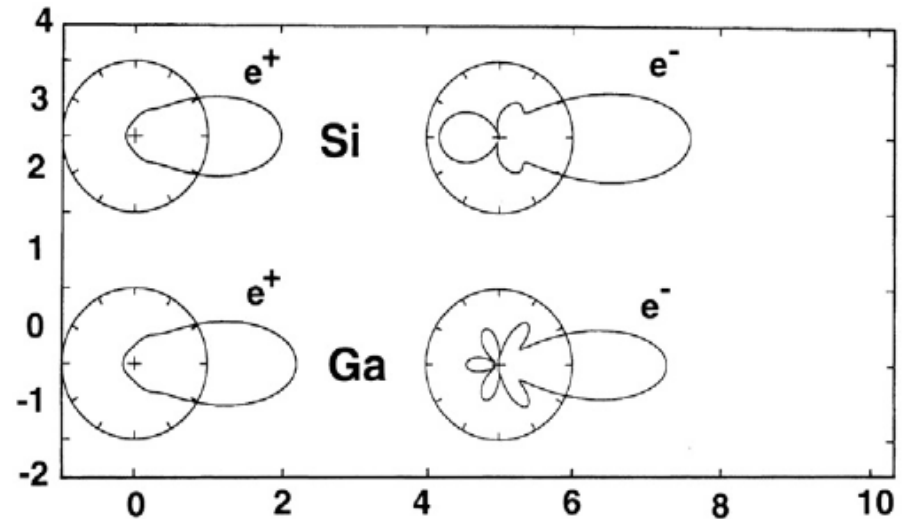
 <p style="text-align: center;">e+ sample screen</p>	 <p style="text-align: center;">screen sample</p>	 <p style="text-align: center;">screen e+ sample</p>
<p style="text-align: center;">TPD Transmission Positron Diffraction</p>	<p style="text-align: center;">LEPD Low Energy Positron Diffraction</p>	<p style="text-align: center;"><u>RHEPD</u> Reflection High Energy Positron Diffraction</p>
<p style="text-align: center;">100keV ▪ 1MeV</p>	<p style="text-align: center;">10 ▪ 500eV</p>	<p style="text-align: center;">10 ▪ 100keV</p>
<p style="text-align: center;">Bulk ▪ Study</p>	<p style="text-align: center;">▪ Surface ▪ Study ▪</p>	

Positron diffraction

- differential scattering factor
- 100 eV e^- and e^+
- Cu



- differential scattering factors
- 100 eV e^- and e^+
- Si, Ga

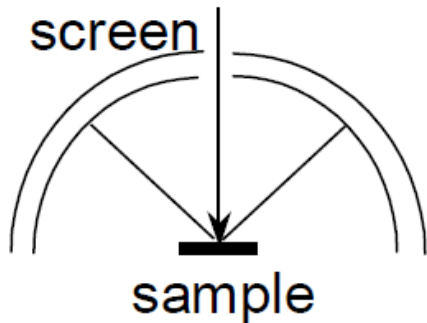


• positrons

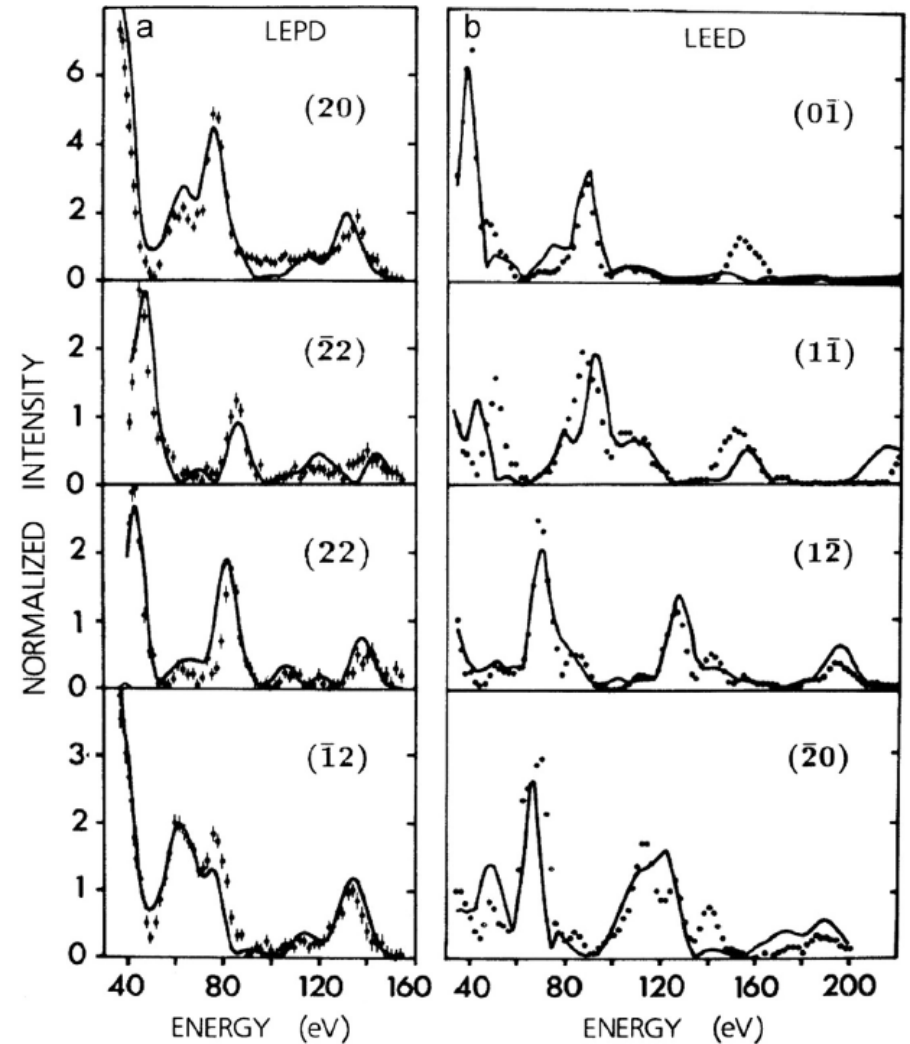
- lower elemental sensitivity
- lower penetration depth, turning point $R_t = \frac{Ze^2}{E_k}$
- low anisotropy

LEPD = Low Energy Positron Diffraction

- I - V curves: intensity of fixed Bragg peak when kinetic energy of incident positrons is varied

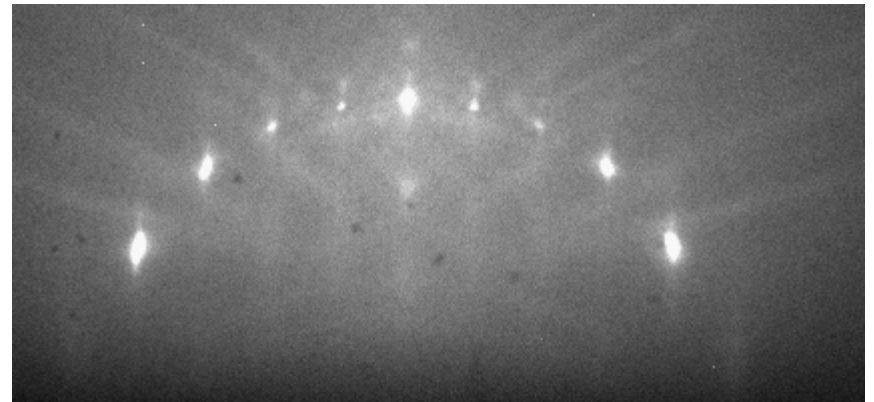
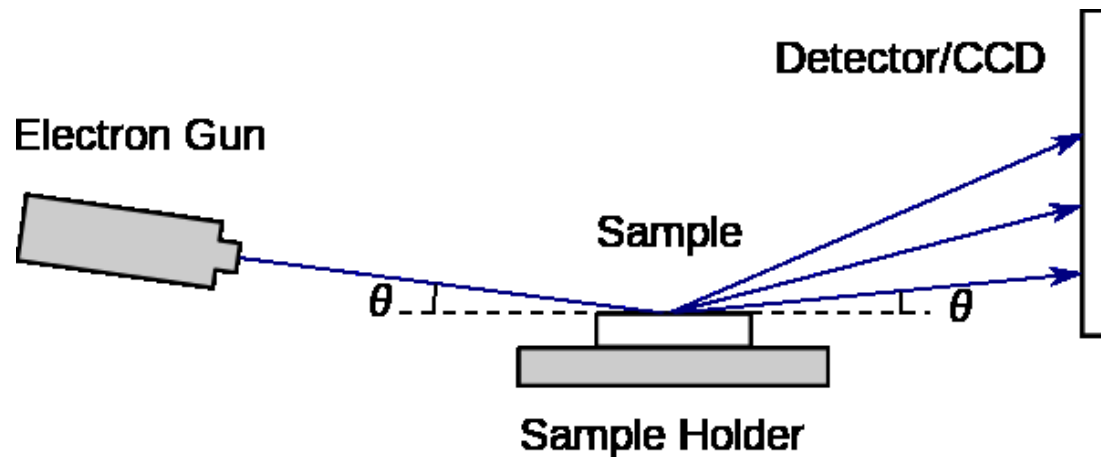
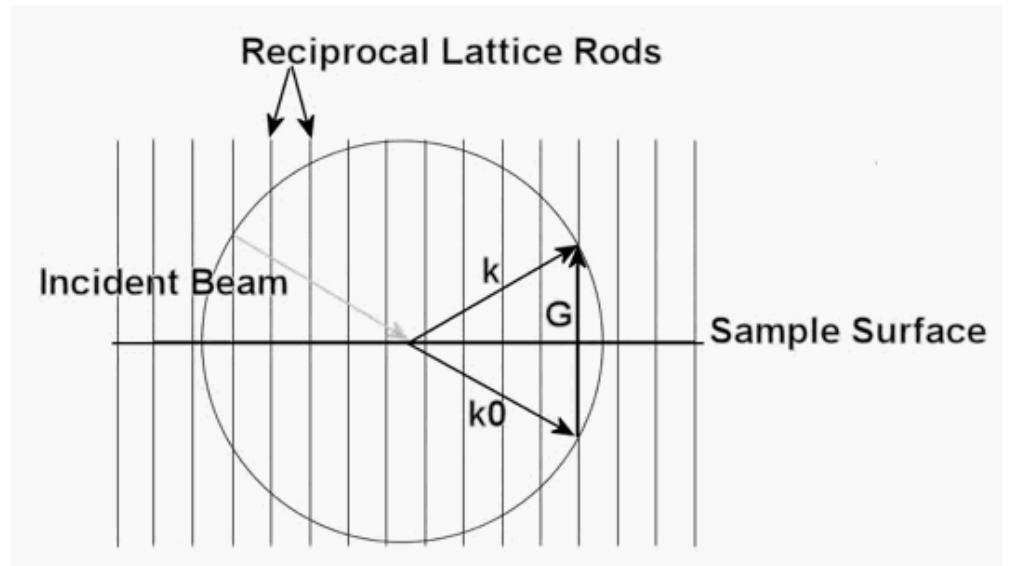


CdSe (11-20) surface



RHEPD = Reflection High-Energy Positron Diffraction

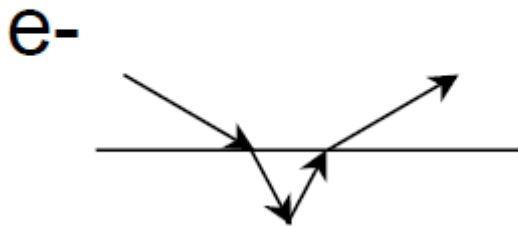
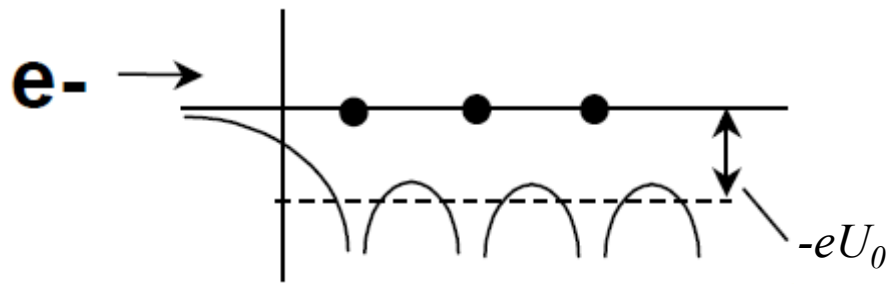
- **electron diffraction on surface**
- quality monitoring of thin films
- kinetic energy of incident particles 10-20 keV



RHEPD = Reflection High-Energy Positron Diffraction

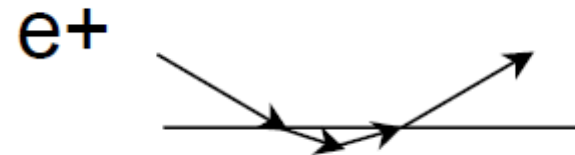
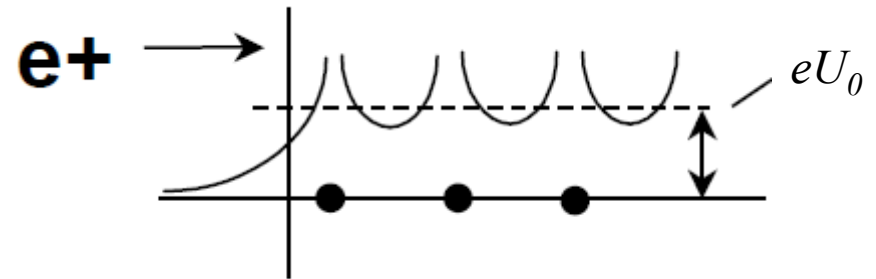
- **electrons**

- potential for electrons
- negative inner potential



- **positrons**

- potential for positrons
- positive inner potential

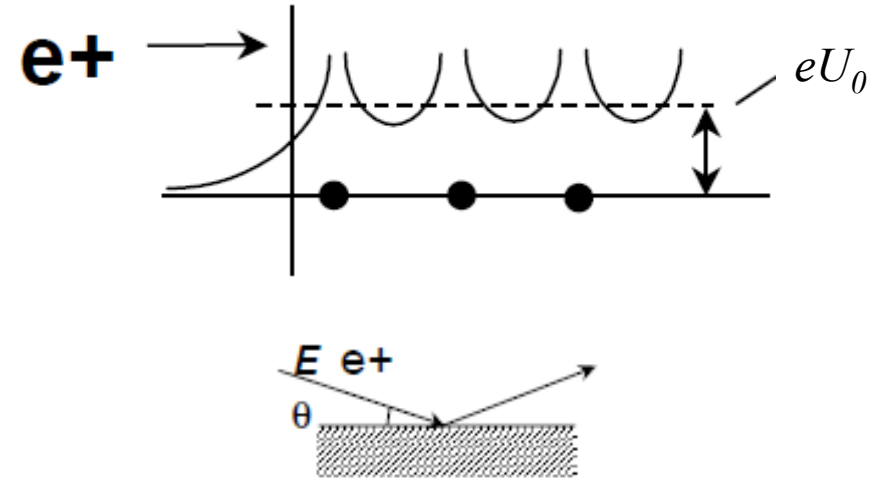


RHEPD = Reflection High-Energy Positron Diffraction

- **RHEPD**

$$\left(-\frac{\hbar^2}{2m}\nabla^2 + eU_0\right)\psi = E\psi$$

- outside crystal $V = 0$
- inside crystal $V > 0$



RHEPD = Reflection High-Energy Positron Diffraction

- Snell law $\frac{\lambda}{\lambda_s} = \frac{\cos \theta}{\cos \theta_s}$

- de Broglie wavelength

- Bragg condition $2d \sin \theta_s = k\lambda_s$

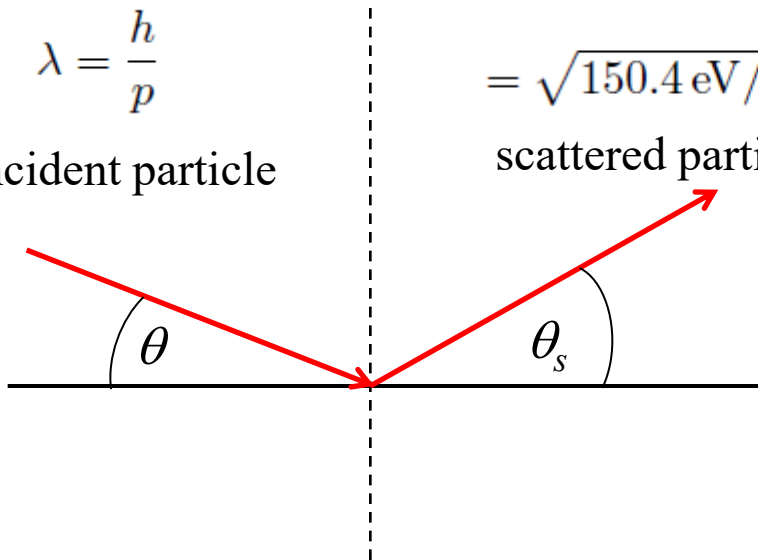
- inter-planar distance

$$\lambda_s = \frac{h}{p_s} = \frac{h}{\sqrt{2m(E_k - qU_0)}}$$

$$= \sqrt{150.4 \text{ eV} / (E_k - qU_0)} \text{ \AA}$$

$\lambda = \frac{h}{p}$
incident particle

scattered particle



- Bragg condition for e^+ or e^- scattering

$$E_k \sin^2 \theta = \frac{k^2}{d^2} 37.5 \text{ \AA}^2 \text{ eV} + qU_0$$

- example:

$$\text{Si: } qU_0 = \pm 12 \text{ eV}, d = 3.14 \text{ \AA}$$

- electron scattering $qU_0 < 0$

$$E_k \sin^2 \theta < 0$$

**first order Bragg peak ($k = 1$)
from surface parallel planes not visible**

RHEPD = Reflection High-Energy Positron Diffraction

- Snell law $\frac{\lambda}{\lambda_s} = \frac{\cos \theta}{\cos \theta_s}$

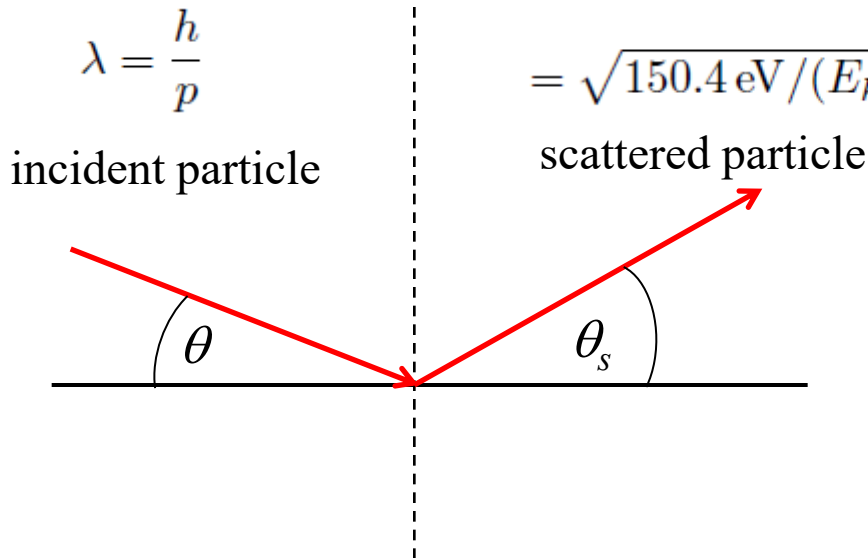
- de Broglie wavelength

- Bragg condition $2d \sin \theta_s = k\lambda_s$

- inter-planar distance

$$\lambda_s = \frac{h}{p_s} = \frac{h}{\sqrt{2m(E_k - qU_0)}}$$

$$= \sqrt{150.4 \text{ eV} / (E_k - qU_0)} \text{ \AA}$$



- Bragg condition for e^+ or e^- scattering

$$E_k \sin^2 \theta = \frac{k^2}{d^2} 37.5 \text{ \AA}^2 \text{ eV} + qU_0$$

- example:

$$\text{Si: } qU_0 = \pm 12 \text{ eV}, d = 3.14 \text{ \AA}$$

- positron scattering $qU_0 > 0$

$$E_k \sin^2 \theta > 0$$

**first order Bragg peak ($k = 1$)
observable**

- **total reflection critical angle**

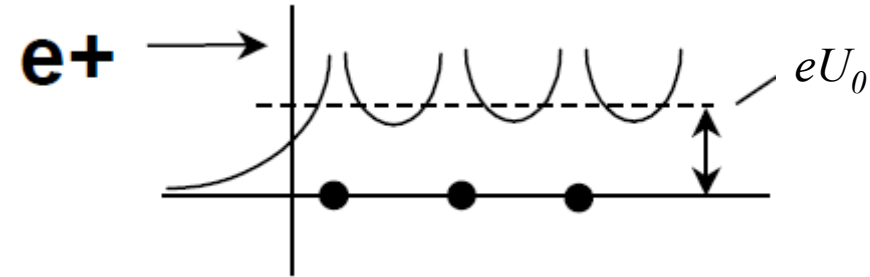
$$\theta_C = \arcsin \left(\sqrt{eU_0 / E_k} \right)$$

RHEPD = Reflection High-Energy Positron Diffraction

- **RHEPD**

$$\left(-\frac{\hbar}{2m}\nabla^2 + eU_0\right)\psi = E\psi$$

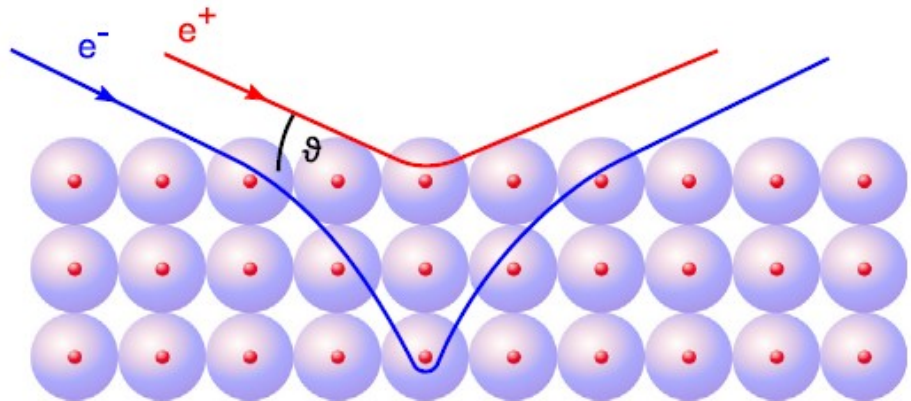
- outside crystal $V = 0$
- inside crystal $V > 0$



- **total positron reflection**

$$\theta_C = \arcsin\left(\sqrt{eU_0/E_k}\right)$$

- positron wave vector can be decomposed into longitudinal and transversal component



$$E_k = \frac{p^2}{2m} = \frac{h^2 k^2}{2m} = \frac{h^2 k_L^2}{2m} + \frac{h^2 k_T^2}{2m} = E_{k,L} + E_{k,T}$$

$$E_{k,T} = E_k \sin^2 \theta \quad \longrightarrow \quad \theta_C = \arcsin\left(\sqrt{eU_0/E_k}\right)$$

RHEPD = Reflection High-Energy Positron Diffraction

- **RHEPD**

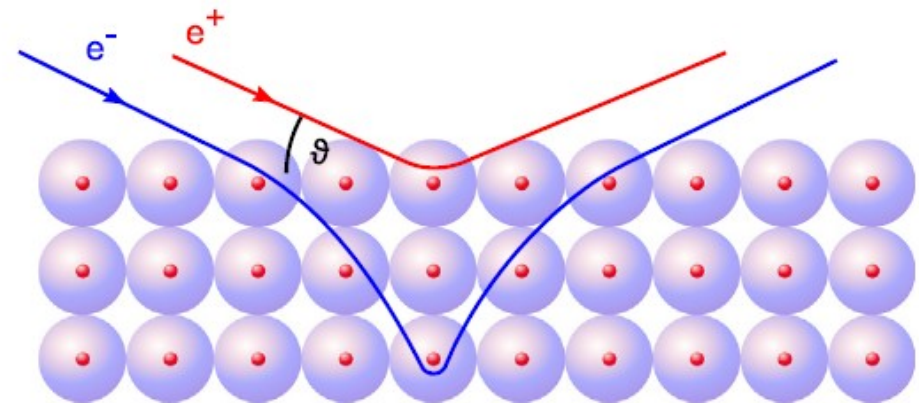
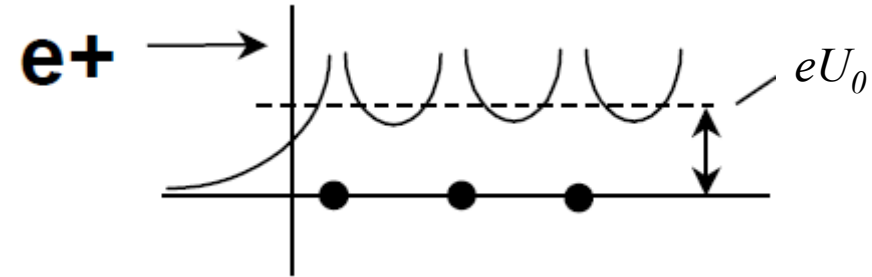
$$\left(-\frac{\hbar}{2m}\nabla^2 + eU_0\right)\psi = E\psi$$

- outside crystal $V = 0$
- inside crystal $V > 0$

- **total positron reflection**

$$\theta_C = \arcsin\left(\sqrt{eU_0/E_k}\right)$$

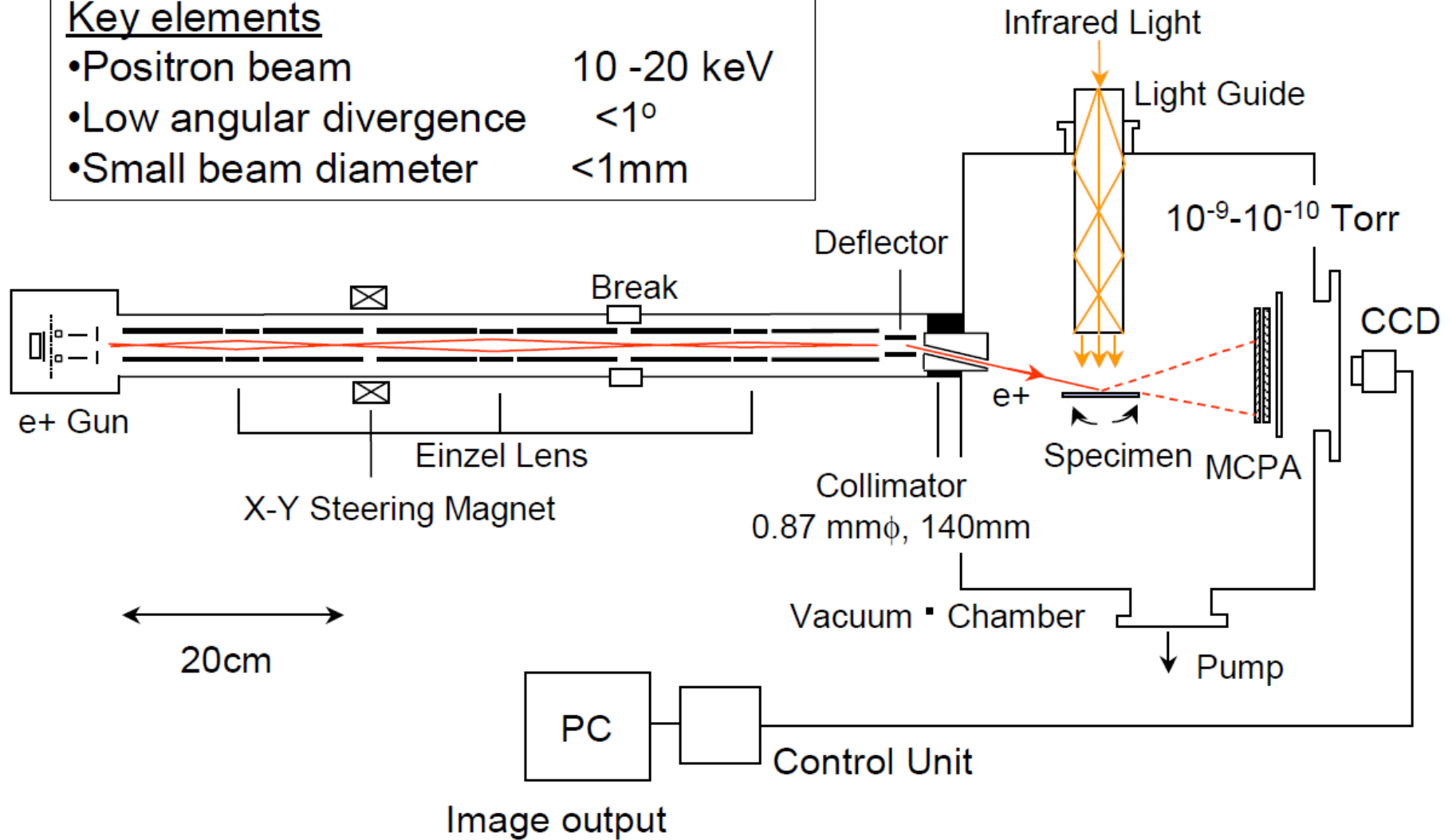
- example Si: $\theta_C = 2^\circ$ for 10 keV positrons



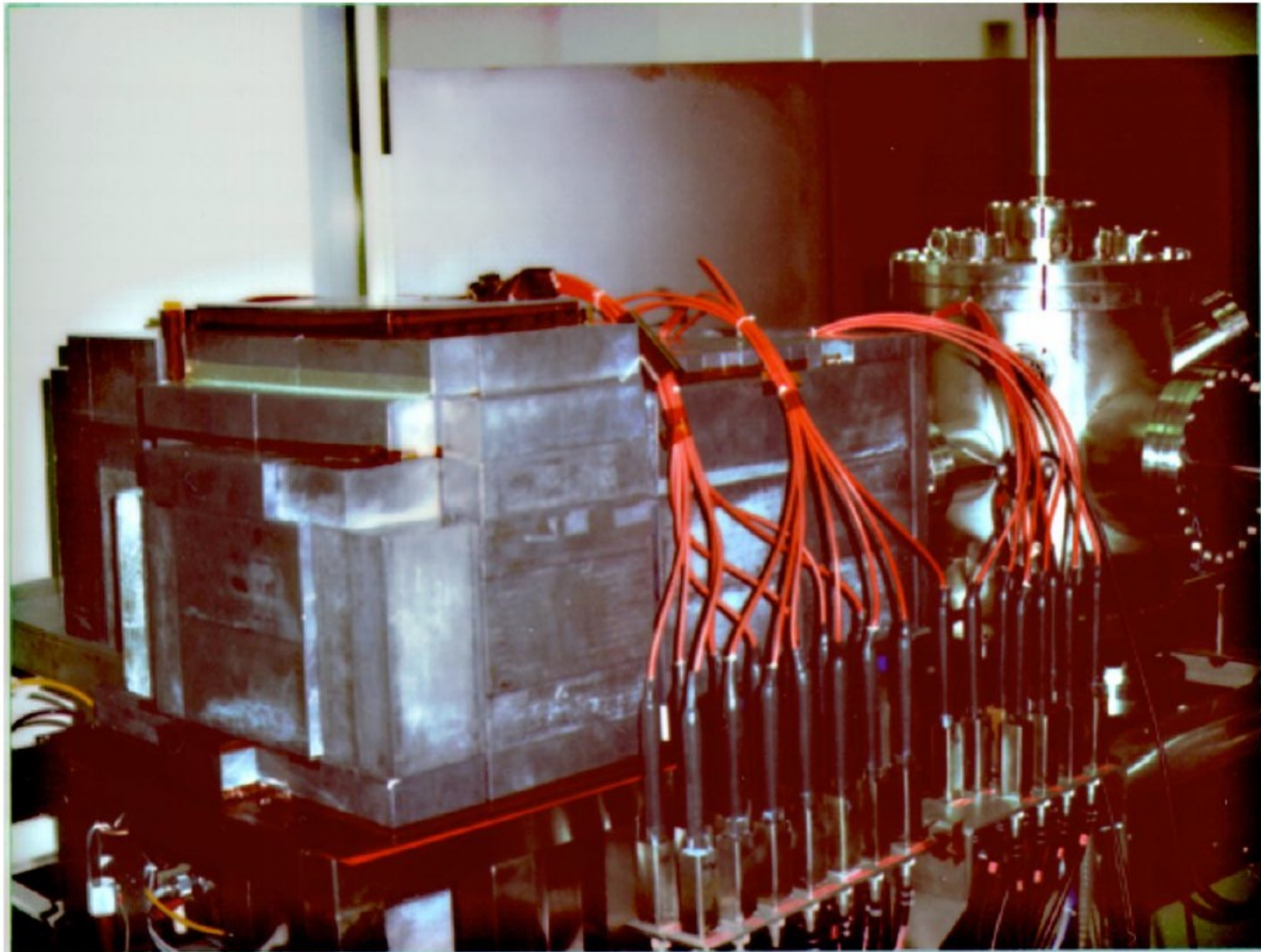
RHEPD = Reflection High-Energy Positron Diffraction

Key elements

- Positron beam 10 -20 keV
- Low angular divergence $<1^\circ$
- Small beam diameter $<1\text{mm}$

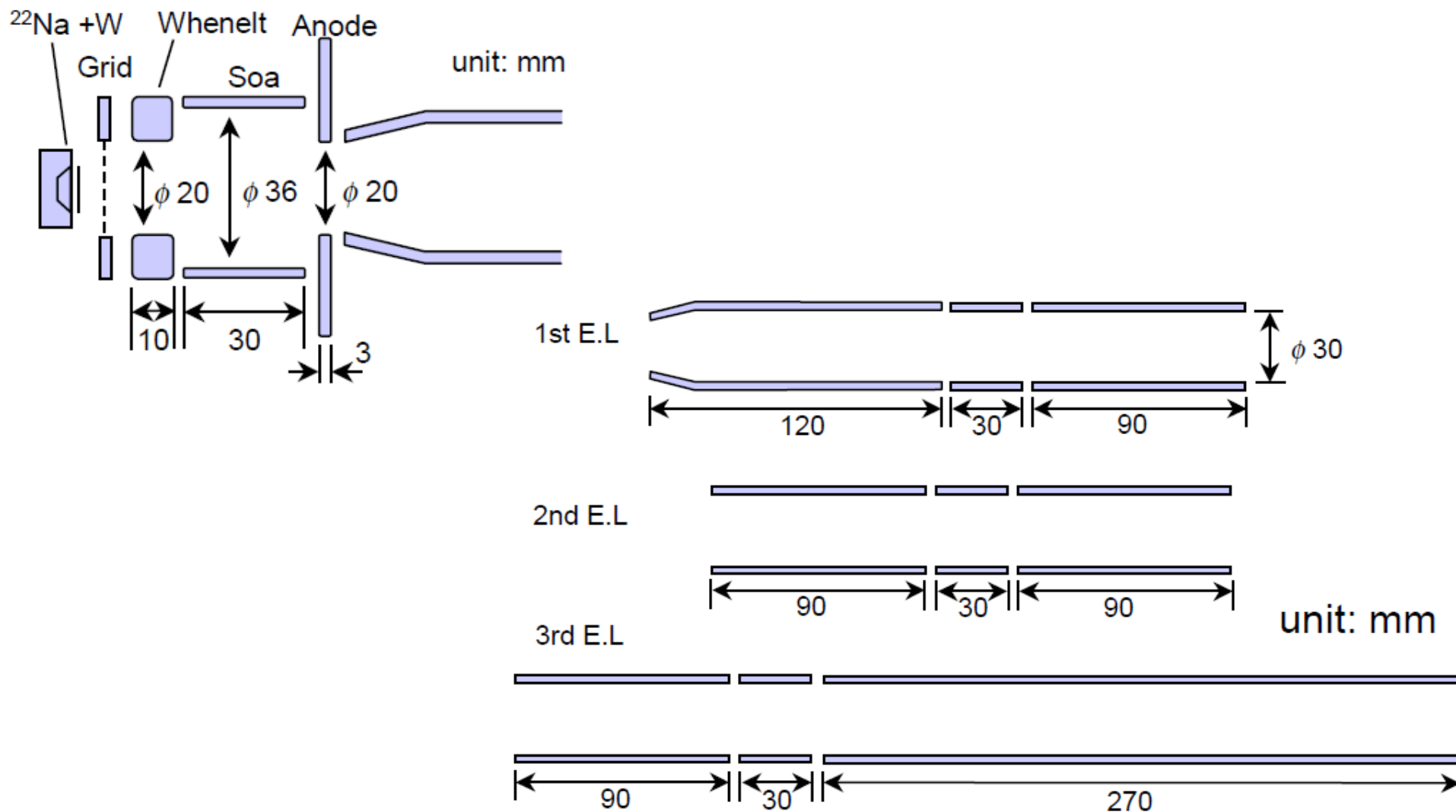


RHEPD = Reflection High-Energy Positron Diffraction



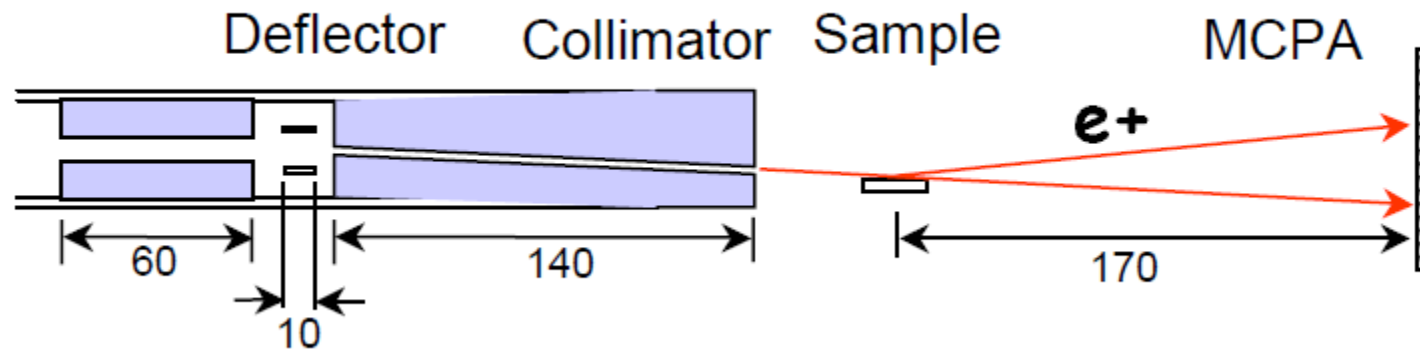
RHEPD = Reflection High-Energy Positron Diffraction

- electrostatically guided beam



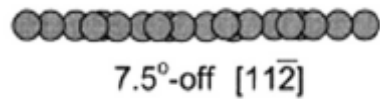
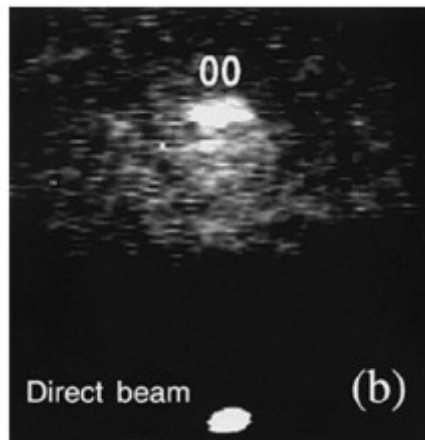
RHEPD = Reflection High-Energy Positron Diffraction

- electrostatically guided beam

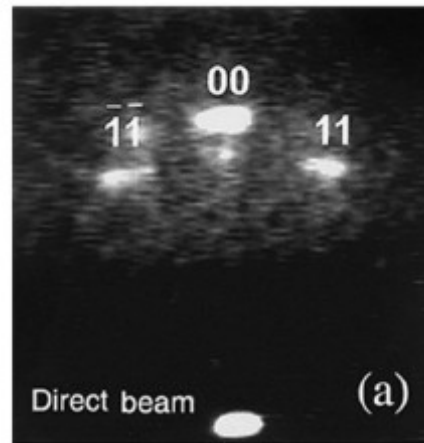


RHEPD = Reflection High-Energy Positron Diffraction

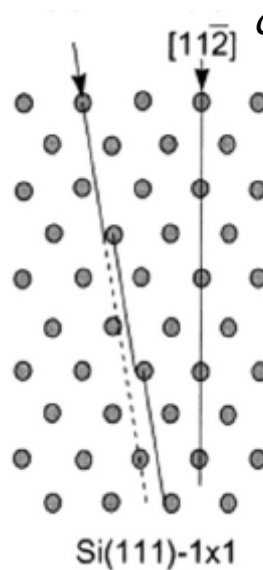
- Si (111)
unreconstructed surface



7.5° off [11-2] direction
one beam condition



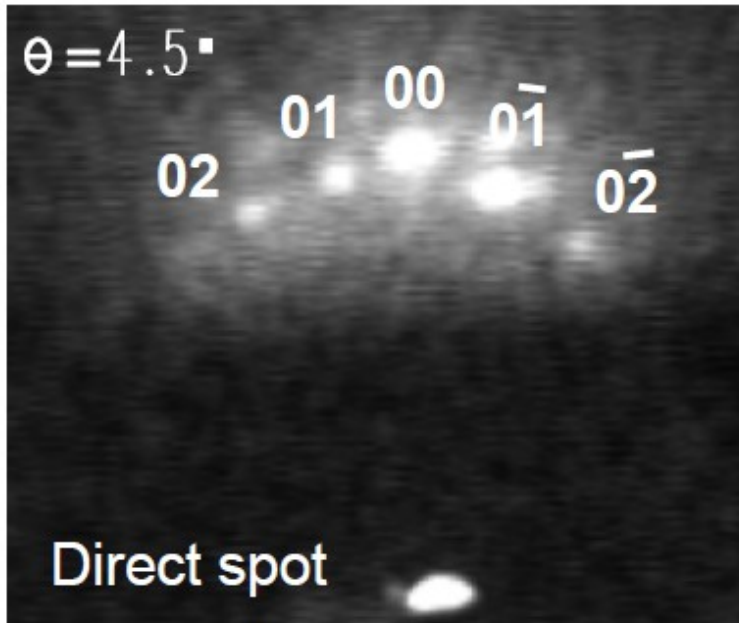
many beam condition



RHEPD = Reflection High-Energy Positron Diffraction

- Si (111) H

RHEPD

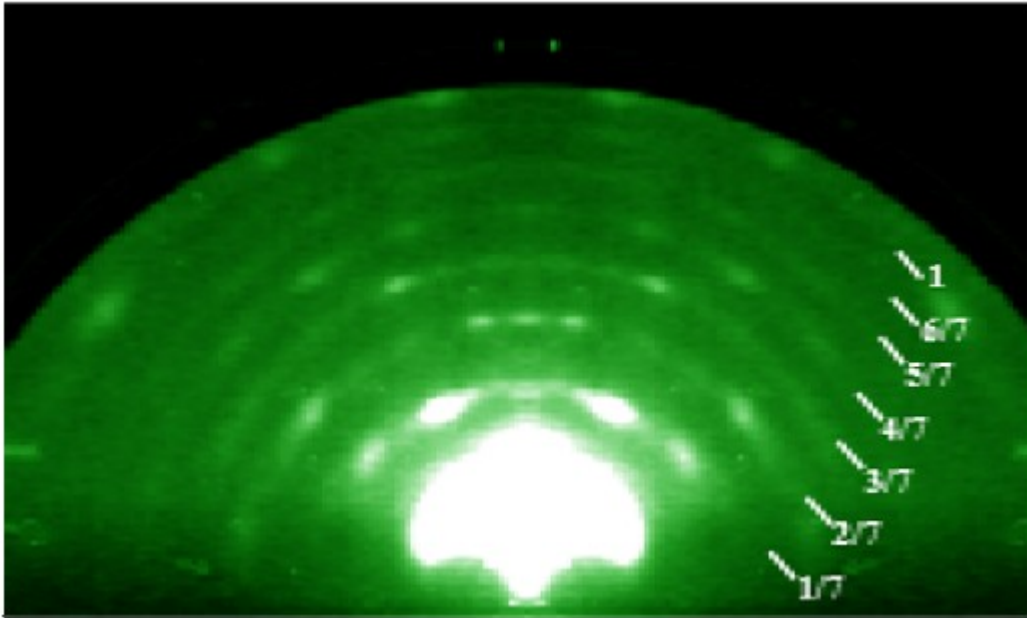


RHEED



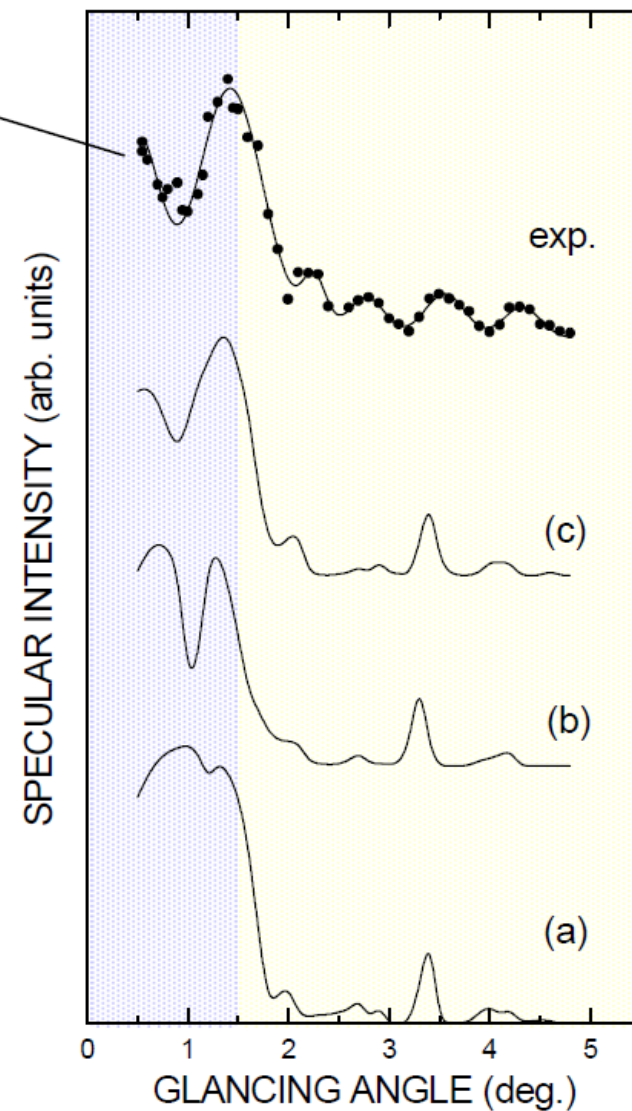
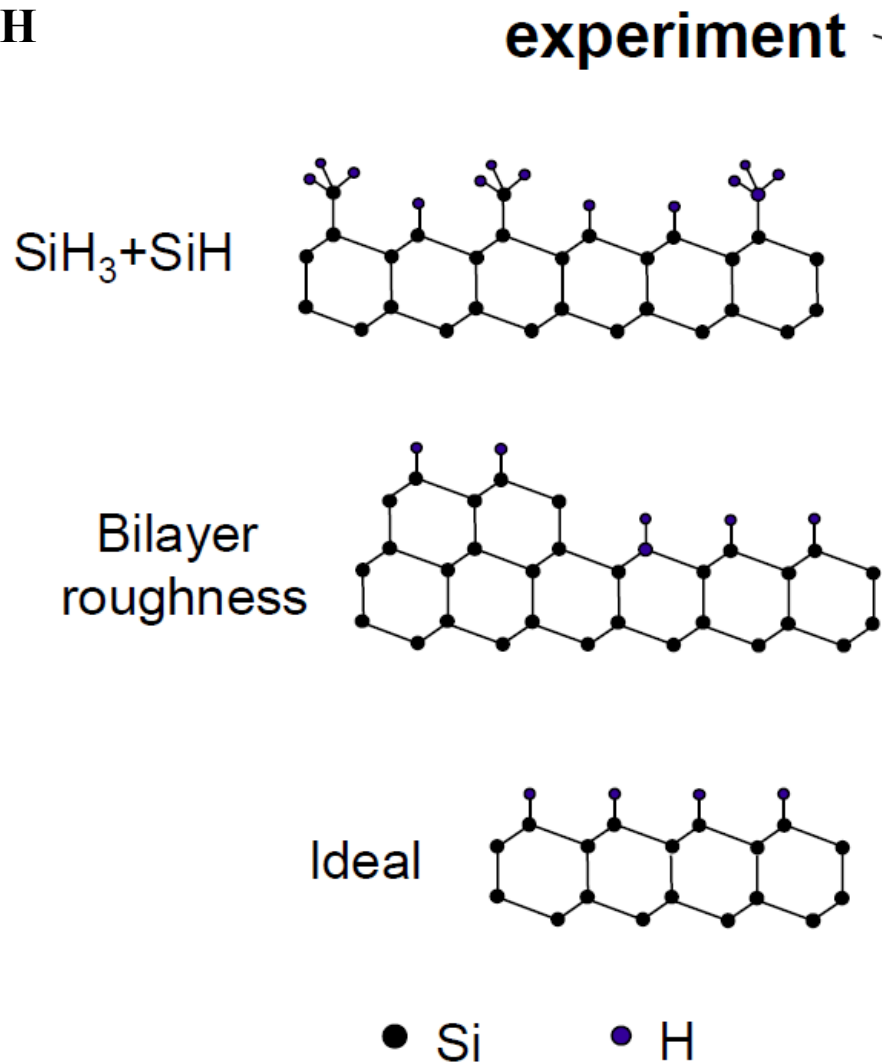
RHEPD = Reflection High-Energy Positron Diffraction

- Rocking curve
- Si (111) H



RHEPD = Reflection High-Energy Positron Diffraction

- Rocking curve
- Si (111) H

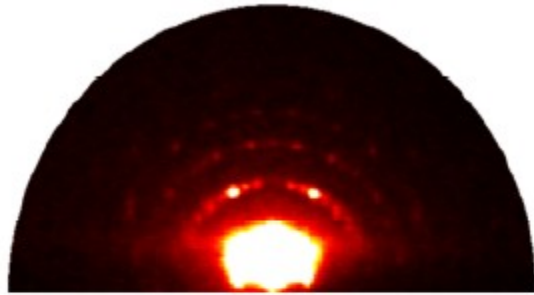


TRHEPD = Total Reflection High-Energy Positron Diffraction

- Si (111) 7 x 7 reconstructed surface

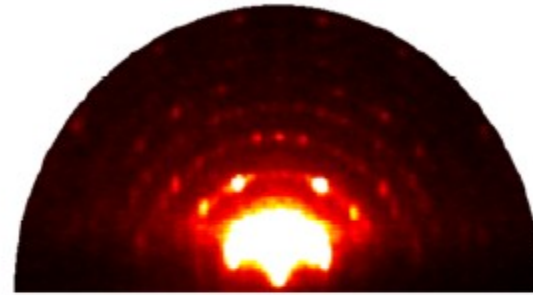
TRHEPD

(1) $\theta = 1.3^\circ$ (total reflection)

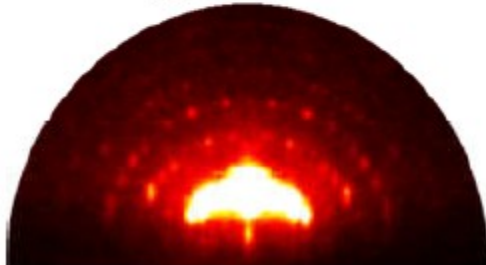


RHEPD

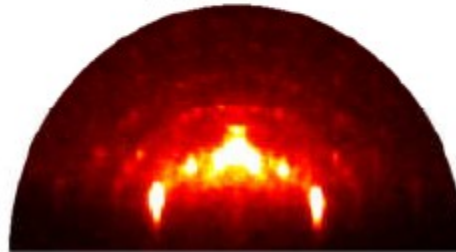
(2) $\theta = 2.1^\circ$



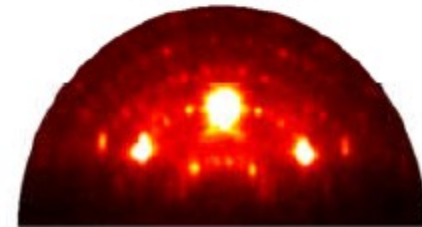
(3) $\theta = 2.9^\circ$



(4) $\theta = 3.9^\circ$

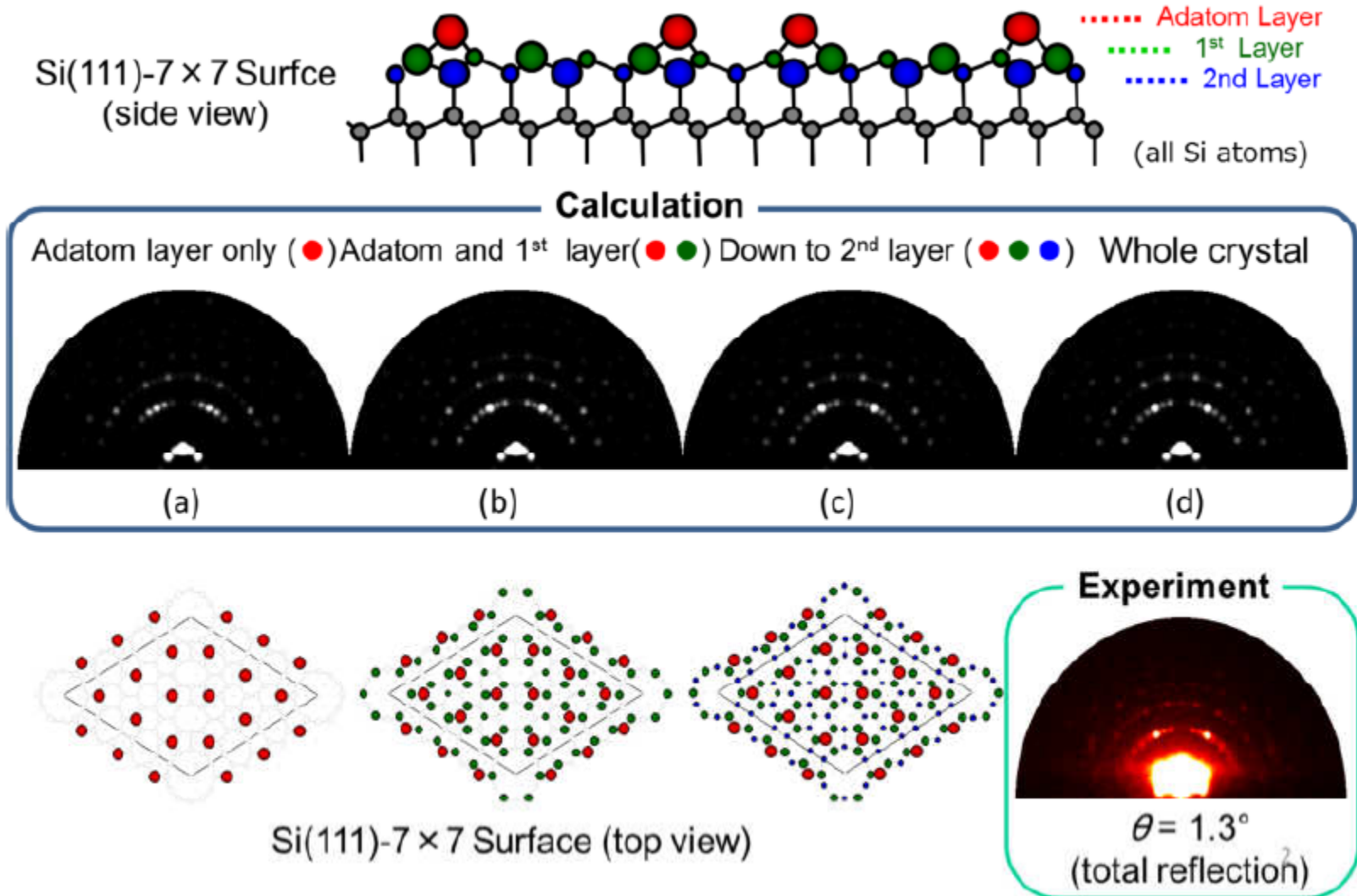


(5) $\theta = 4.9^\circ$



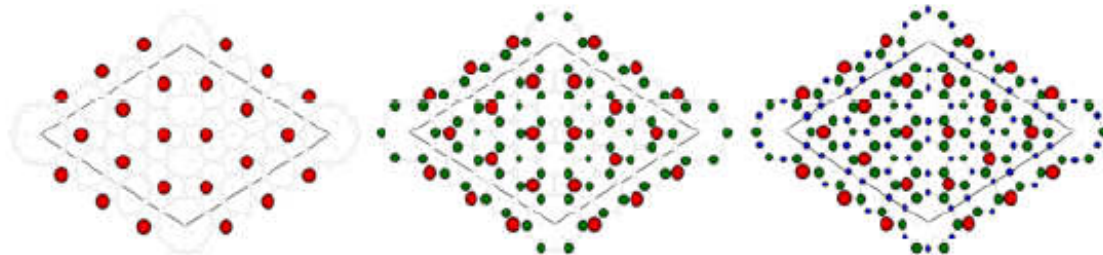
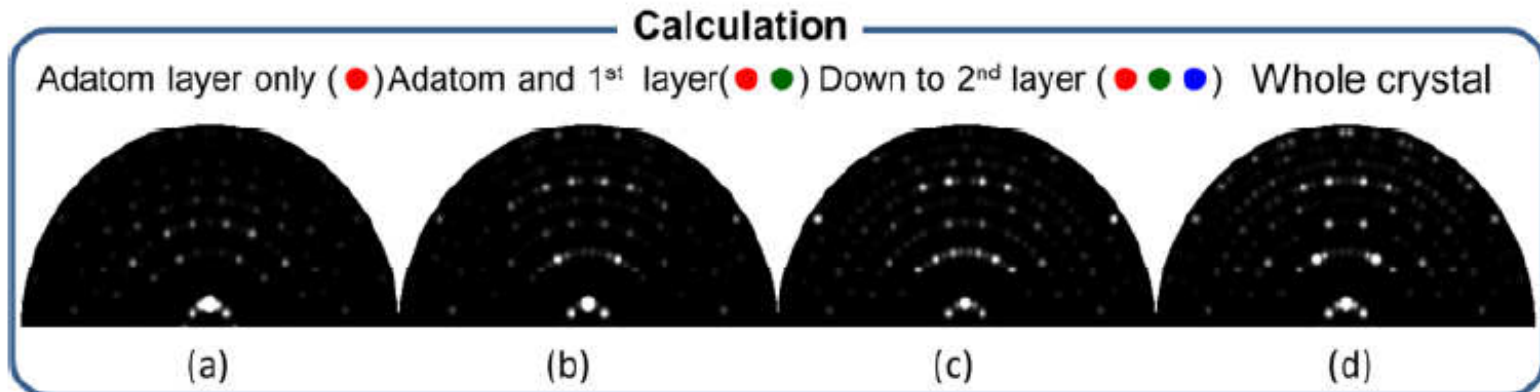
TRHEPD = Total Reflection High-Energy Positron Diffraction

- Si (111) 7 x 7 reconstructed surface TRHEPD

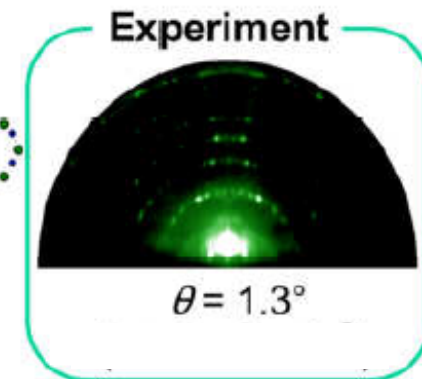


RHEED = Reflection High-Energy Electron Diffraction

- Si (111) 7 x 7 reconstructed surface RHEED



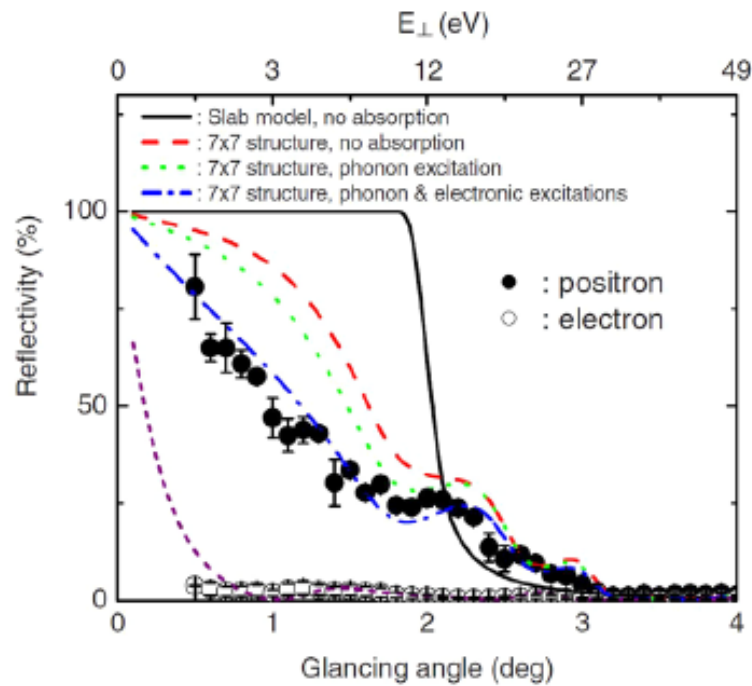
Si(111)-7 x 7 Surface (top view)



RHEED = Reflection High-Energy Electron Diffraction

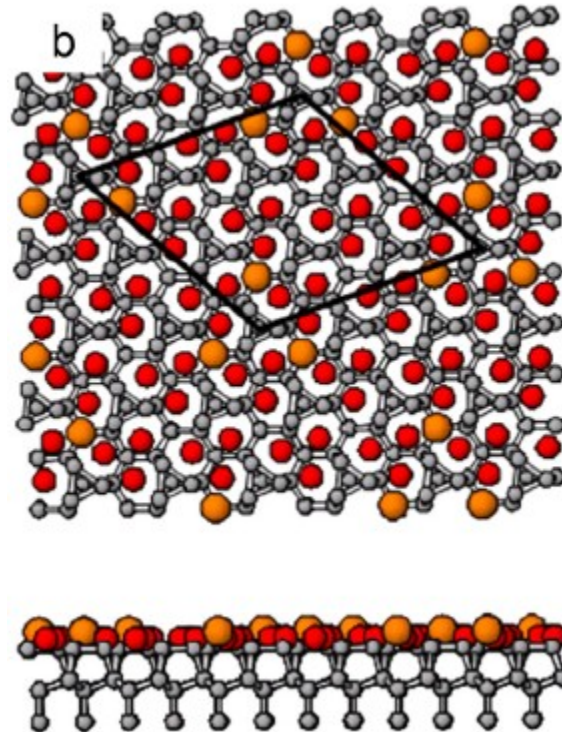
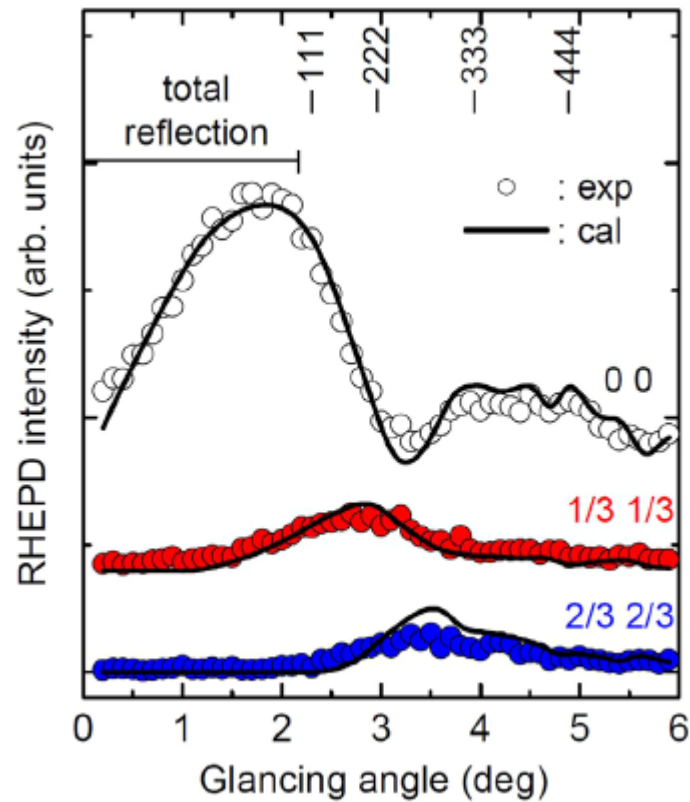
- Si (111) 7 x 7 reconstructed surface

absolute reflectivness



RHEED = Reflection High-Energy Electron Diffraction

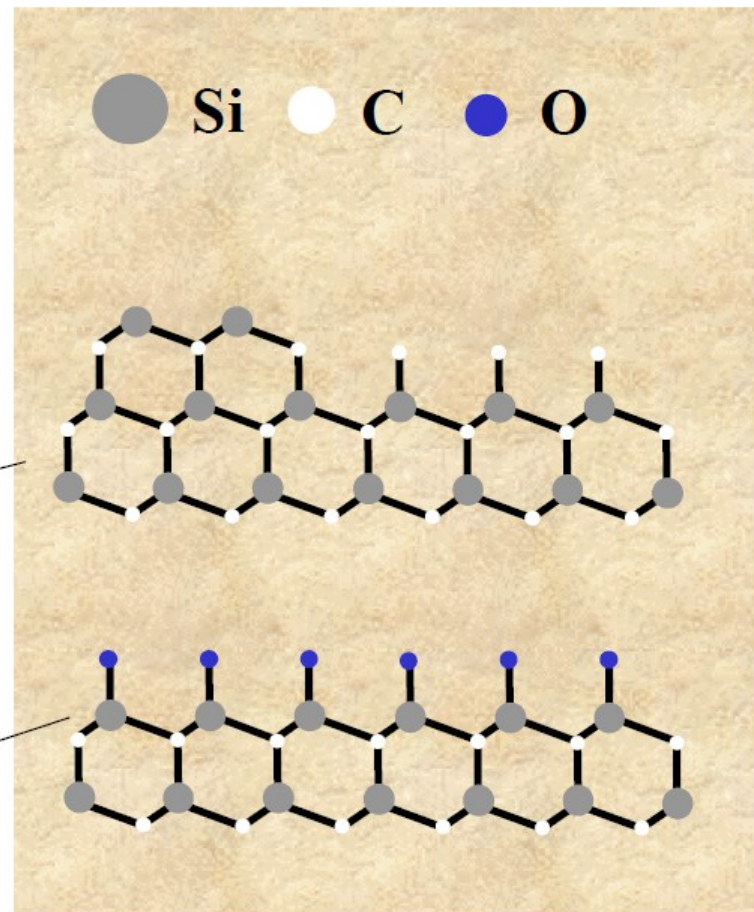
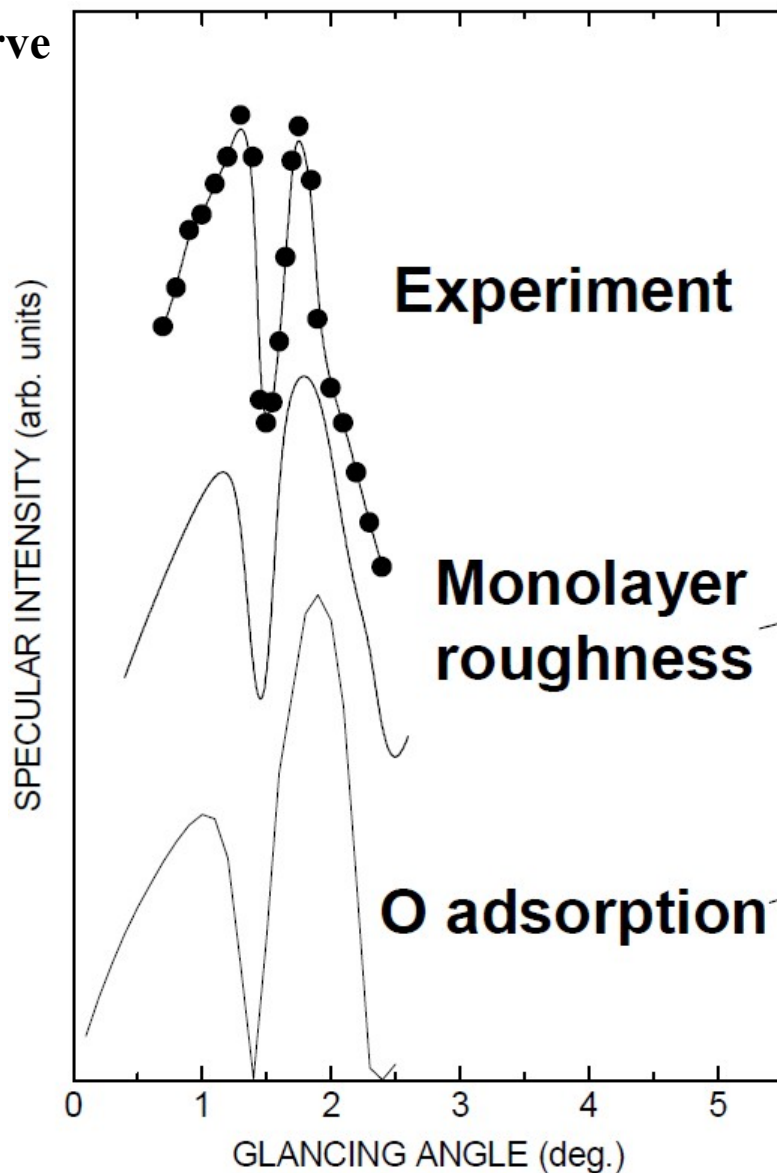
$$\text{Si}(111) - \sqrt{21} \times \sqrt{21} - \text{Ag}$$



- many beam condition

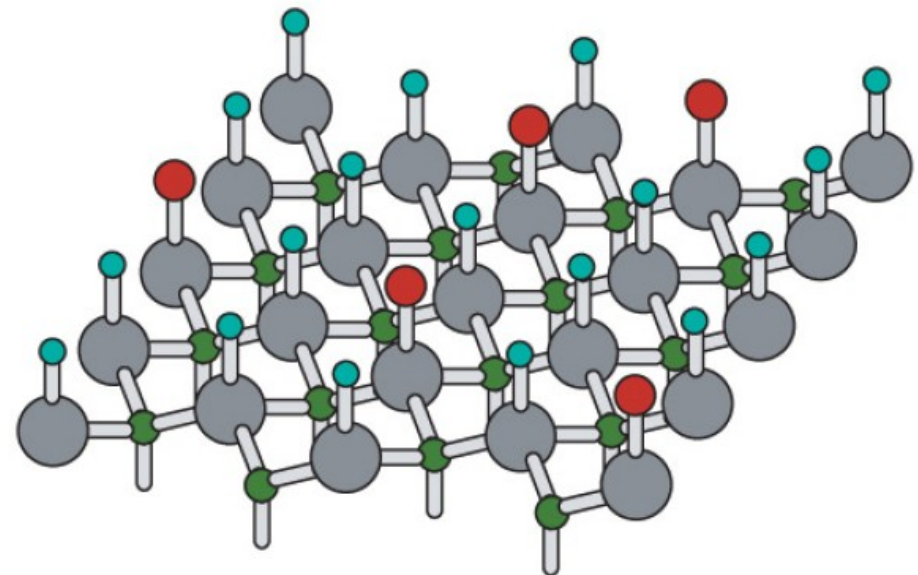
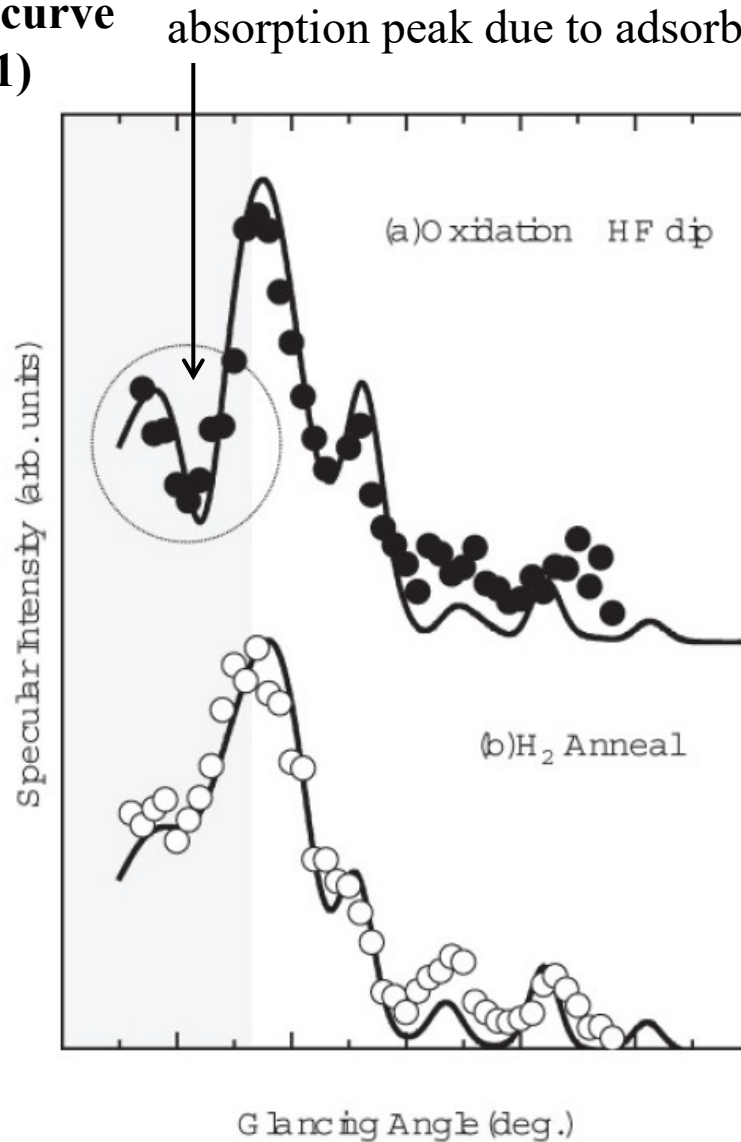
RHEPD = Reflection High-Energy Positron Diffraction

- Rocking curve
- SiC (0001)



RHEPD = Reflection High-Energy Positron Diffraction

- **Rocking curve**
- **SiC (0001)**



(c)

RHEPD = Reflection High-Energy Positron Diffraction

- **Rocking curve** Flashing by infra red lamp at 1020°C in UHV → full covering by graphite monolayer
- **SiC (0001)**

